

IXYS DSEC60-12A High Performance Fast Recovery Diode **Owner's Manual**

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IXYS DSEC60-12A High Performance Fast Recovery Diode



Product Information

Specifications:

• Part Number: DSEC60-12A

VRSM: 1,12 VVRRM: 16 mV

IR: 0,25 AVF: 12 VIFAV: 200 A

• RMS Current: 70 A

• Virtual Junction Temperature: -55 to 150°C

Operation Temperature: -55 to 150°C
Storage Temperature: -55 to 150°C

Features:

- Planar passivated chips
- Very low leakage current
- · Very short recovery time
- Improved thermal behavior
- Low Irm-values
- · Soft recovery behavior
- Avalanche voltage rated for reliable operation

Applications:

- · Antiparallel diode for high frequency switching devices
- · Antisaturation diode
- Snubber diode
- Free-wheeling diode

- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

- TO-247
- · Industry standard outline
- · RoHS compliant
- Epoxy meets UL 94V-0

Product Usage Instructions

Mounting Instructions:

- 1. Ensure proper heat dissipation by mounting on a suitable heatsink.
- 2. Use the recommended mounting torque of 0.8-1.2 Nm.
- 3. Avoid applying excessive force during mounting to prevent damage.

Circuit Connection:

Connect the diode according to the application requirements, ensuring correct polarity and connections.

Operating Conditions:

- Operate within the specified temperature range of -55 to 150°C.
- Avoid exceeding the maximum RMS current rating of 70 A.

FAQ (Frequently Asked Questions)

What are the key features of the DSEC60-12A diode?

The key features include planar passivated chips, very low leakage current, very short recovery time, improved thermal behavior, and soft recovery behavior.

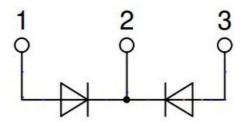
What applications is the DSEC60-12A diode suitable for?

The diode is suitable for use as an antiparallel diode for high frequency switching devices, antisaturation diode, snubber diode, free-wheeling diode, rectifiers in switch mode power supplies (SMPS), and uninterruptible power supplies (UPS).

· What is the recommended mounting torque for the TO-247 package?

The recommended mounting torque is between 0.8 and 1.2 Nm.

CIRCUIT DIAGRAM



Features / Advantages

- Planar passivated chips
- · Very low leakage current
- · Very short recovery time
- · Improved thermal behaviour
- · Very low Irm-values
- · Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- · Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications

- Antiparallel diode for high frequency switching devices
- · Antisaturation diode
- Snubber diode
- · Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package TO-247

- · Industry standard outline
- · RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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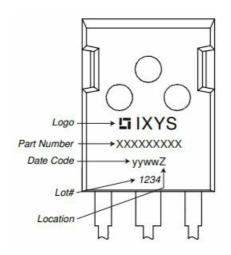
Fast Diode

Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse block	ring voltage	$T_{VJ} = 25^{\circ}C$		347	1200	V
V _{RRM}	max. repetitive reverse blocking v	voltage	$T_{VJ} = 25^{\circ}C$. 95	1200	٧
I _R	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$. 20	250	μΑ
		V _R = 1200 V	$T_{VJ} = 150^{\circ}C$			1	mA
V _F	forward voltage drop	I _F = 30 A	$T_{VJ} = 25^{\circ}C$		- 33	2,74	V
		$I_F = 60 \text{ A}$				3,27	٧
		I _F = 30 A	T _{VJ} = 150°C			1,79	٧
		$I_F = 60 \text{ A}$				2,30	٧
IFAV	average forward current	T _C = 120°C	$T_{VJ} = 175^{\circ}C$			30	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		$T_{VJ} = 175^{\circ}C$			1,12	٧
r _F	slope resistance } for power lo	oss calculation only				16	mΩ
RthJC	thermal resistance junction to case	se				0,9	K/W
R _{thCH}	thermal resistance case to heatsi	ink			0,25		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			165	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			200	Α
CJ	junction capacitance	$V_R = 600 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		12		pF
I _{RM}	max. reverse recovery current	Y	$T_{VJ} = 25^{\circ}C$		8,5		Α
		$I_{\rm F} = 30 \text{A}; V_{\rm B} = 600 \text{V}$	$T_{VJ} = 100$ °C		13		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 30 \text{ A}; V_R = 600 \text{ V} \\ -di_F/dt = 200 \text{ A}/\mu\text{s} \end{cases}$	$T_{VJ} = 25^{\circ}C$		60		ns
18826)	$T_{VJ} = 100$ °C		170		ns

SYMBOLS IDENTIFICATION

Packag e	TO-247		Ratings				
Symbol	Definition	Conditions	min	typ.	max	Un it	
I RMS	RMS current	per terminal 1)			70	Α	
TVJ	virtual junction temperatur e		-55		175	°C	
Тор	operation temperature		-55		150	°C	
Tstg	storage temperature		-55		150	°C	
Weight			6		g		
MD	mounting torque		0,8		1,2	N m	
F C	mounting force with clip		20		120	N	

Product Marking

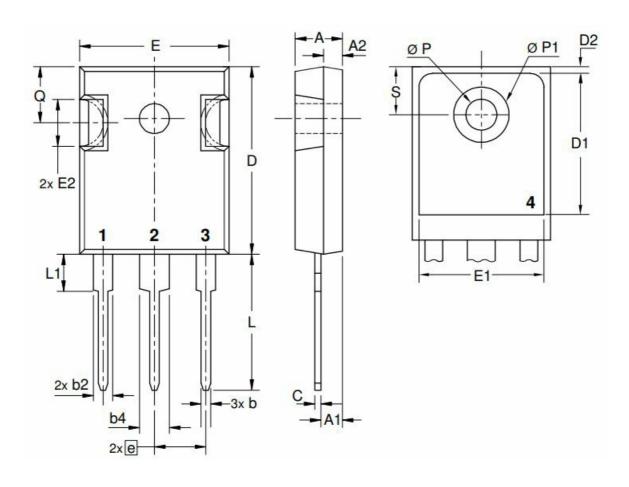


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantit y	Code N o.	
Standard	DSEC60-12A	DSEC60-12A	Tube	30	476412	

Equivalent Circuits for Simulation

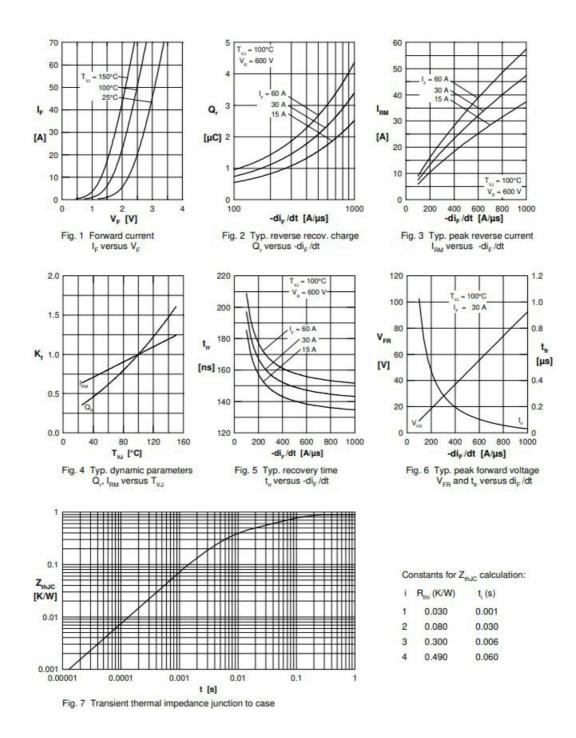
1			* on die level	$T_{VJ} = 175^{\circ}C$
$I \rightarrow V_0$	R _o -	Fast Diode		
V _{0 max}	threshold voltage	1,12		V
R _{0 max}	slope resistance *	13,4		$m\Omega$

DIMENSION



Sym.	Inches		Millimeter min. max	,	
Sylli.	min. max.		willineter filli. Illaz	. .	
Α	0.185	0.209	4.70	5.30	
A1	0.087	0.102	2.21	2.59	
A2	0.059	0.098	1.50	2.49	
D	0.819 0.845		20.79 21.45		
E	0.610 0.640		15.48 16.24		
E2	0.170 0.216		4.31 5.48		
е	0.215 BSC		5.46 BSC		
L	0.780 0.800 19.8		19.80 20.30		
L1	- 0.177		- 4.49		
Ø P	0.140 0.144 3.55 3.65				
Q	0.212 0.244		5.38 6.19		
S	0.242 BSC		6.14 BSC		
b	0.039	0.055	0.99	1.40	
b2	0.065	0.094	1.65	2.39	
b4	0.102	0.135	2.59	3.43	
С	0.015	0.035	0.38	0.89	
D1	0.515	_	13.07	_	
D2	0.020	0.053	0.51	1.35	
E1	0.530	_	13.45	_	
Ø P1	_	0.29	_	7.39	

Fast Diode



Documents / Resources



IXYS DSEC60-12A High Performance Fast Recovery Diode [pdf] Owner's Manual DSEC60-12A High Performance Fast Recovery Diode, DSEC60-12A, High Performance Fast Recovery Diode, Fast Recovery Diode, Recovery Diode

References

- **Product Disclaimer**
- User Manual

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